



**DMN3052L** 

#### N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

#### **Features**

Low On-Resistance:

$$\begin{split} R_{DS(ON)} &< 32 m\Omega @ V_{GS} = 10V \\ R_{DS(ON)} &< 42 m\Omega @ V_{GS} = 4.5V \\ R_{DS(ON)} &< 64 m\Omega @ V_{GS} = 2.5V \end{split}$$

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

• Case: SOT-23

- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe.
  Solderable per MIL-STD-202, Method 208

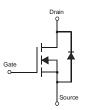
Terminal Connections: See Diagram

- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)

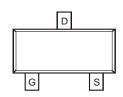
SOT-23







**Equivalent Circuit** 



TOP VIEW

### **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Drain Source Voltage		$V_{DSS}$	30	V
Gate-Source Voltage		V <sub>GSS</sub>	±12	V
Drain Current (Note 1)	$T_A = 25$ °C $T_A = 70$ °C	I <sub>D</sub>	5.4 4.6	А
Drain Current (Note 1)	Pulsed	I <sub>DM</sub>	19	А
Body-Diode Continuous Current (Note 1)		Is	2.0	Α

### Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	P <sub>D</sub>	1.4	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C (Note 1)	$R_{ hetaJA}$	90	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

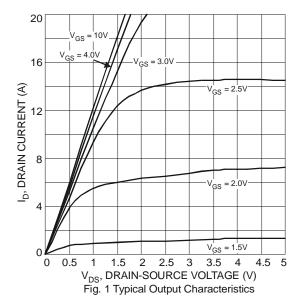
- 1. Device mounted on FR-4 PCB. t ≤5 sec.
- 2. No purposefully added lead.
- 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

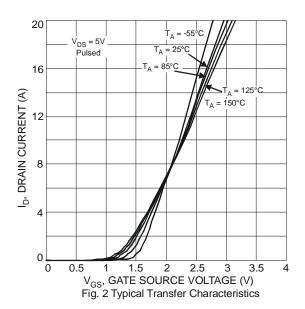


### Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 4)								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_D = 250 \mu A$		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	1	μА	$V_{DS} = 30V, V_{GS} = 0V$		
Gate-Body Leakage	I <sub>GSS</sub>	-	_	±80 ±800	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$ $V_{GS} = \pm 19V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 4)								
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.62	0.9	1.2	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$		
		_	26	32		$V_{GS} = 10V, I_D = 5.8A$		
Static Drain-Source On-Resistance	Pro (ON)	_	33	42	mΩ	$V_{GS} = 4.5V, I_D = 5.0A$		
otatic Brain Gource On Resistance	R <sub>DS</sub> (ON)	_	52	64		$V_{GS} = 2.5V, I_D = 3.8A$		
			78	100		$V_{GS} = 2.0V, I_D = 2.0A$		
Forward Transconductance	Y <sub>fs</sub>		8	_	S	$V_{DS} = 5V, I_{D} = 3.1A$		
Source-Drain Diode Forward Voltage			0.75	1.2	V	$V_{GS} = 0V, I_{S} = 2.0A$		
Source-Drain Diode Forward Voltage $V_{SD}$ — $0.75$   1.2   $V$   $V_{GS}$ = 0V, $I_S$ = 2.0A <b>DYNAMIC CHARACTERISTICS</b>								
Input Capacitance	C <sub>iss</sub>	_	555	_	pF	., 5), ),		
Output Capacitance	Coss	_	109	_	pF	$V_{DS} = 5V, V_{GS} = 0V$ -f = 1.0MHz		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	82	_	pF	1 = 1.0WI1Z		
Total Gate Charge			6.3	_		\\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \		
Gate-Source Charge	$Q_{gs}$		1.3	_	nC	$V_{GS} = 4.5V, V_{DS} = 15V,$ $I_{D} = 5.8A$		
Gate-Drain Charge	Q <sub>gd</sub>		1.7			ID = 0.0A		

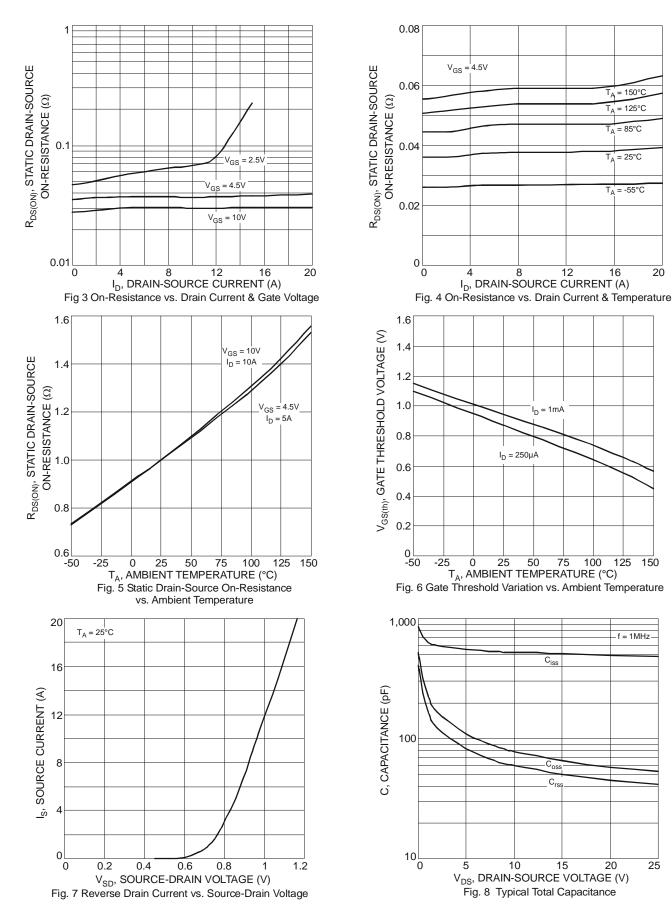
Notes: 4. Short duration pulse test used to minimize self-heating effect.





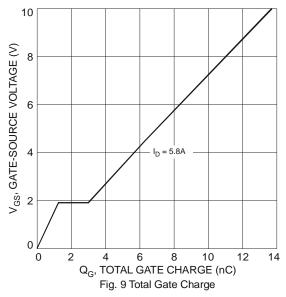
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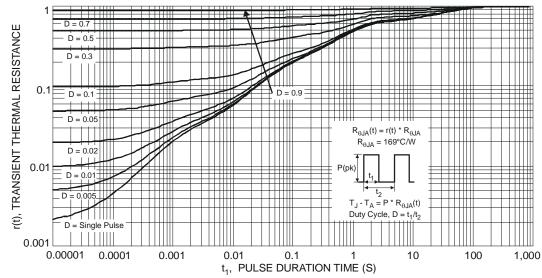


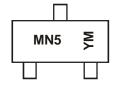
Fig. 10 Transient Thermal Resistance

## Ordering Information (Note 5)

Part Number	Case	Packaging
DMN3052L-7	SOT-23	3000/Tape & Reel

 $Notes: \hspace{0.5cm} \textbf{5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.} \\$ 

## **Marking Information**



MN5 = Product Type Marking Code YM = Date Code Marking

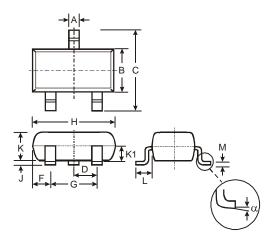
Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

Date Code Key

Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	X		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Au	g Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

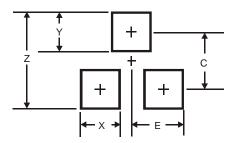


## **Package Outline Dimensions**



	SOT-23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.903	1.10	1.00				
K1	-	1	0.400				
L	0.45	0.61	0.55				
M	0.085	0.18	0.11				
α	0°	8°	-				
All	All Dimensions in mm						

# **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
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